

Electronic Supplementary Information

Manipulating the charge transfer at CuPc/graphene interface by O₂ plasma treatments

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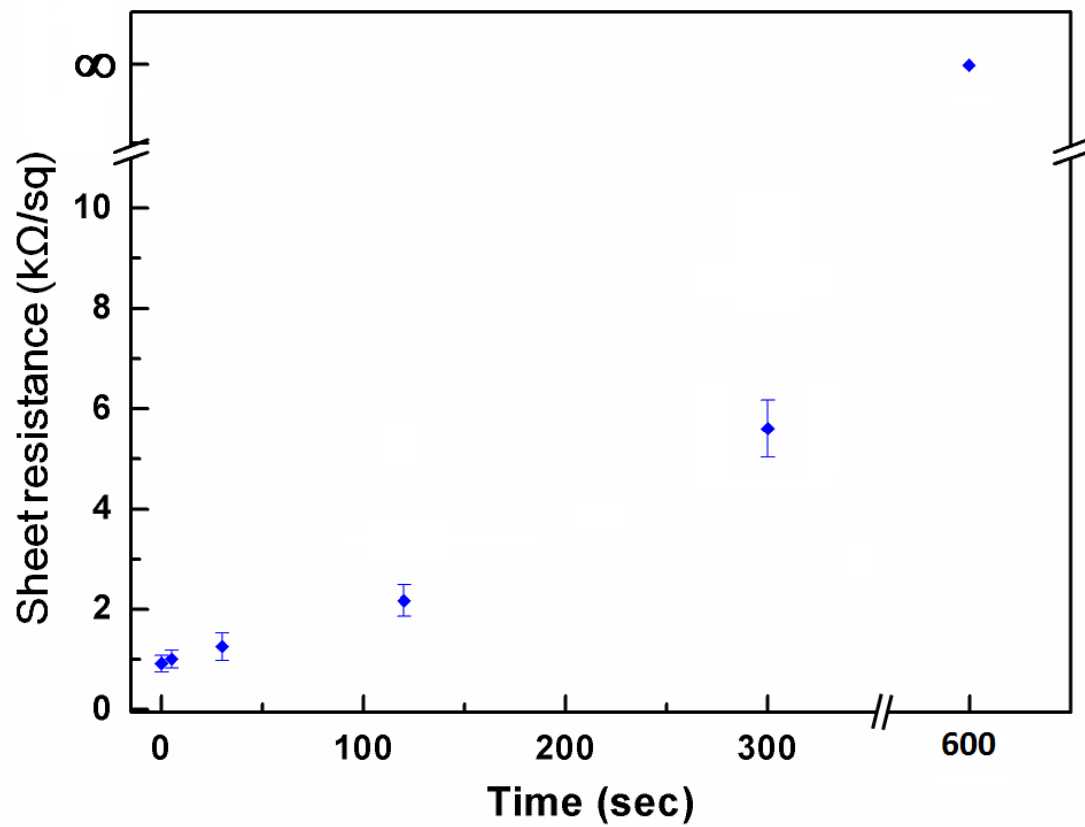


Figure S1 The sheet resistance of pristine graphene and O₂-G with increasing O₂ plasma exposure time.

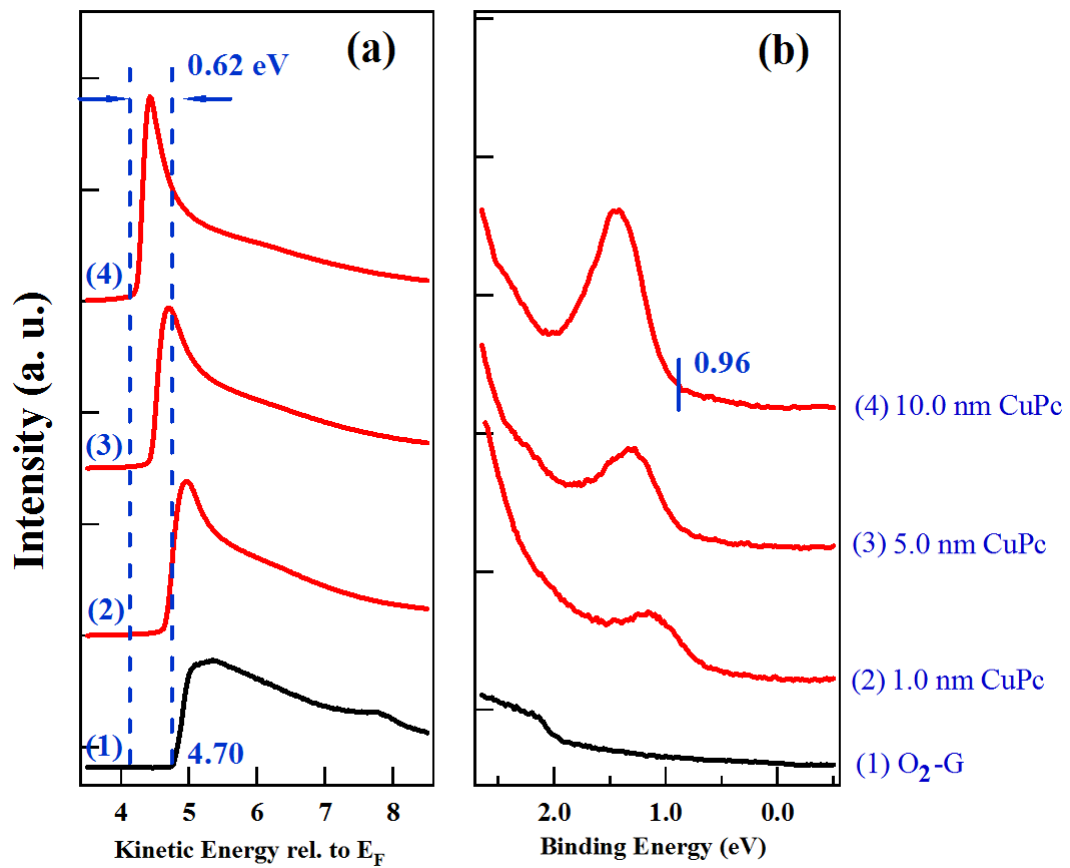


Figure S2 UPS spectra at (a) the low kinetic energy region (secondary electron cutoff), and (b) the low binding energy region (valence band region) during the sequential deposition of 10.0 nm CuPc on graphene sample exposed to O_2 plasma (2 W) for 120 s.